

High Efficiency LED in \varnothing 3 mm Clear Package

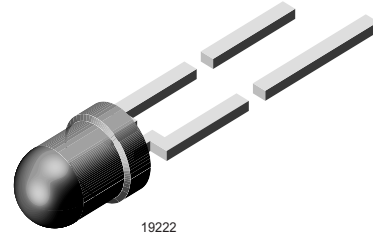
Description

The TLH.4900 series was developed for applications where high light output is required.

It is housed in a 3 mm clear plastic package. The small viewing angle of these devices provides a high brightness.

All LEDs are categorized in luminous intensity groups. The green and yellow LEDs are categorized additionally in wavelength groups.

That allows users to assemble LEDs with uniform appearance.



19222



Features

- Choice of five bright colors
- Standard \varnothing 3 mm (T-1) package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Very small viewing angle
- Luminous intensity categorized
- Yellow and green color categorized
- Lead-free device

Applications

- Status lights
- OFF / ON indicator
- Background illumination
- Readout lights
- Maintenance lights
- Legend light

Parts Table

Part	Color, Luminous Intensity	Angle of Half Intensity ($\pm\phi$)	Technology
TLHR4900	Red, $I_V > 6.3$ mcd	16 °	GaAsP on GaP
TLHO4900	Soft orange, $I_V > 10$ mcd	16 °	GaAsP on GaP
TLHY4900	Yellow, $I_V > 10$ mcd	16 °	GaAsP on GaP
TLHG4900	Green, $I_V > 16$ mcd	16 °	GaP on GaP
TLHP4900	Pure green, $I_V > 4$ mcd	16 °	GaP on GaP

Absolute Maximum Ratings

$T_{amb} = 25$ °C, unless otherwise specified

TLHR4900 , TLHO4900 , TLHY4900 , TLHP4900

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	6	V
DC Forward current	$T_{amb} \leq 60$ °C	I_F	30	mA
Surge forward current	$t_p \leq 10$ μ s	I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 60$ °C	P_V	100	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C

Parameter	Test condition	Symbol	Value	Unit
Storage temperature range		T_{stg}	- 55 to + 100	°C
Soldering temperature	$t \leq 5$ s, 2 mm from body	T_{sd}	260	°C
Thermal resistance junction/ambient		R_{thJA}	400	K/W

Optical and Electrical Characteristics

$T_{amb} = 25$ °C, unless otherwise specified

Red

TLHR4900

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10$ mA	I_V	6.3	13		mcd
Dominant wavelength	$I_F = 10$ mA	λ_d	612		625	nm
Peak wavelength	$I_F = 10$ mA	λ_p		635		nm
Angle of half intensity	$I_F = 10$ mA	ϕ		± 16		deg
Forward voltage	$I_F = 20$ mA	V_F		2	3	V
Reverse voltage	$I_R = 10$ μ A	V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1$ MHz	C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Soft Orange

TLHO4900

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10$ mA	I_V	10	26		mcd
Dominant wavelength	$I_F = 10$ mA	λ_d	598		611	nm
Peak wavelength	$I_F = 10$ mA	λ_p		605		nm
Angle of half intensity	$I_F = 10$ mA	ϕ		± 16		deg
Forward voltage	$I_F = 20$ mA	V_F		2.4	3	V
Reverse voltage	$I_R = 10$ μ A	V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1$ MHz	C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Yellow

TLHY4900

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10$ mA	I_V	10	26		mcd
Dominant wavelength	$I_F = 10$ mA	λ_d	581		594	nm
Peak wavelength	$I_F = 10$ mA	λ_p		585		nm
Angle of half intensity	$I_F = 10$ mA	ϕ		± 16		deg
Forward voltage	$I_F = 20$ mA	V_F		2.4	3	V
Reverse voltage	$I_R = 10$ μ A	V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1$ MHz	C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Green

TLHG4900

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10 \text{ mA}$	I_V	16	37		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$	λ_d	562		575	nm
Peak wavelength	$I_F = 10 \text{ mA}$	λ_p		565		nm
Angle of half intensity	$I_F = 10 \text{ mA}$	ϕ		± 16		deg
Forward voltage	$I_F = 20 \text{ mA}$	V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	6	15		V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Pure green

TLHP4900

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10 \text{ mA}$	I_V	4	13		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$	λ_d	555		565	nm
Peak wavelength	$I_F = 10 \text{ mA}$	λ_p		555		nm
Angle of half intensity	$I_F = 10 \text{ mA}$	ϕ		± 16		deg
Forward voltage	$I_F = 20 \text{ mA}$	V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	6	15		V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Typical Characteristics ($T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified)

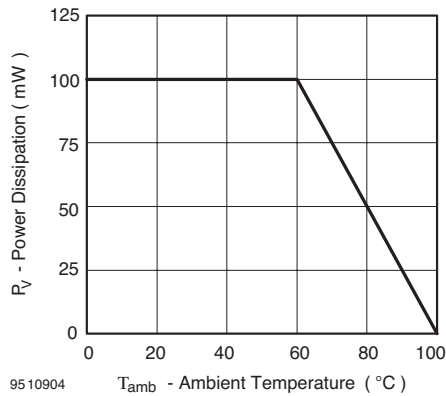


Figure 1. Power Dissipation vs. Ambient Temperature

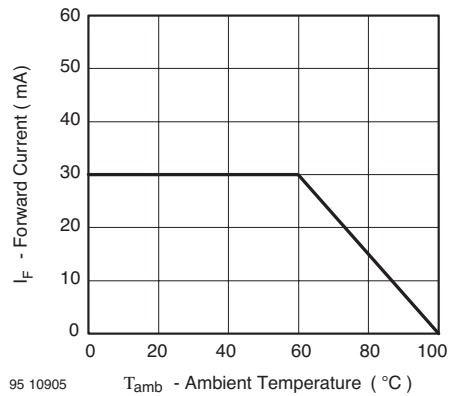


Figure 2. Forward Current vs. Ambient Temperature for InGaN

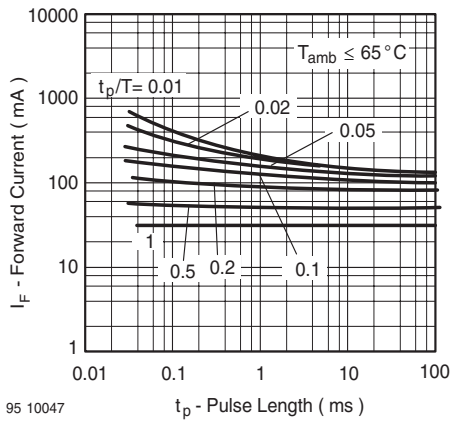


Figure 3. Forward Current vs. Pulse Length

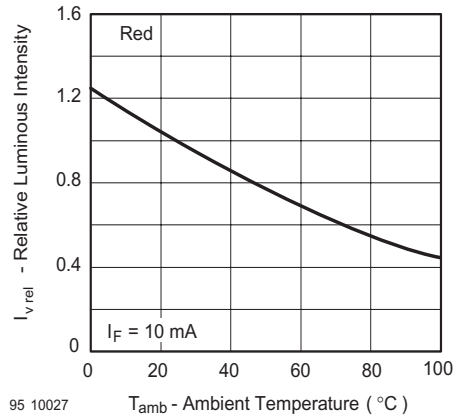


Figure 6. Rel. Luminous Intensity vs. Ambient Temperature

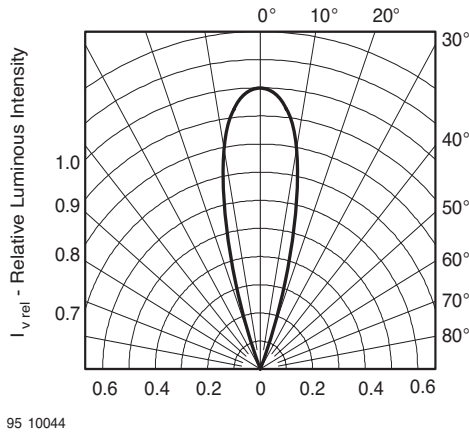


Figure 4. Rel. Luminous Intensity vs. Angular Displacement

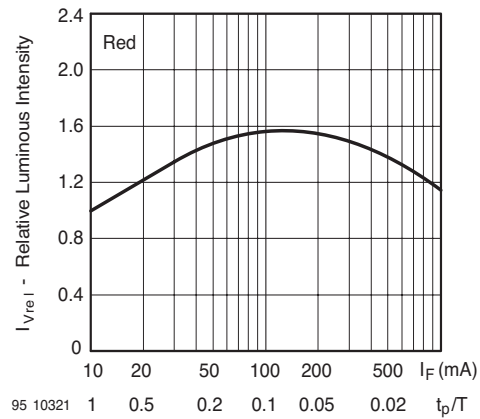


Figure 7. Rel. Luminous Intensity vs. Forw. Current/Duty Cycle

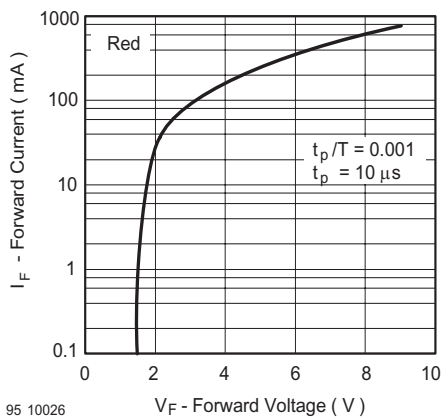


Figure 5. Forward Current vs. Forward Voltage

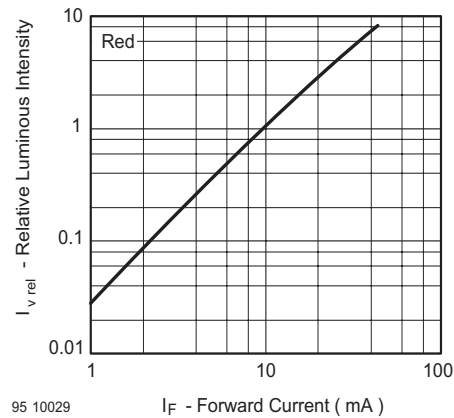


Figure 8. Relative Luminous Intensity vs. Forward Current

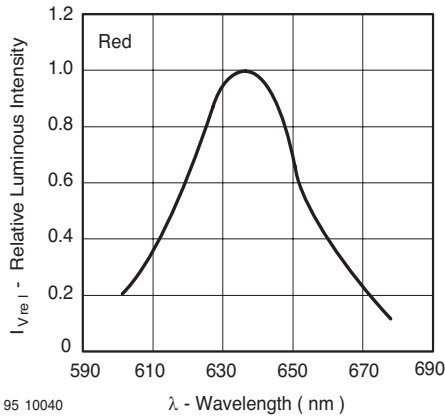


Figure 9. Relative Intensity vs. Wavelength

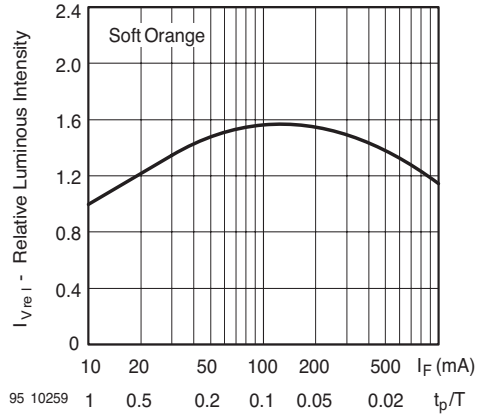


Figure 12. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

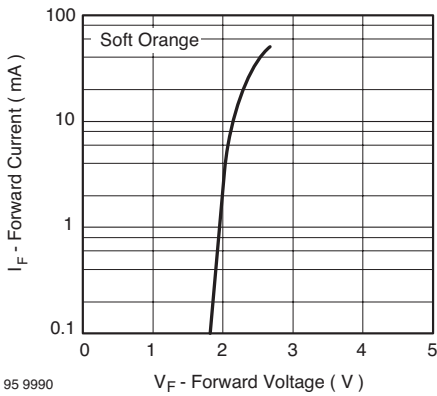


Figure 10. Forward Current vs. Forward Voltage

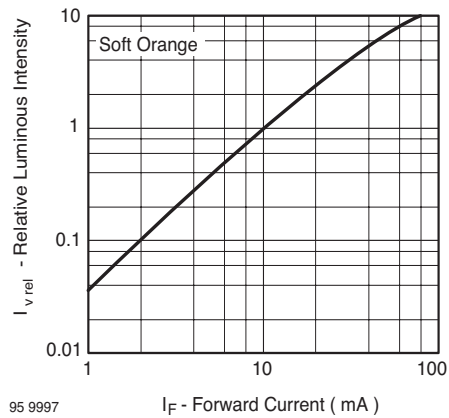


Figure 13. Relative Luminous Intensity vs. Forward Current

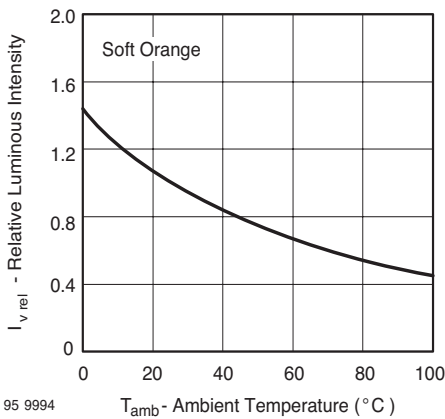


Figure 11. Rel. Luminous Intensity vs. Ambient Temperature

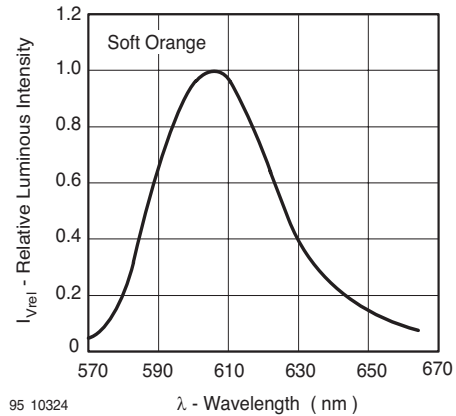


Figure 14. Relative Intensity vs. Wavelength

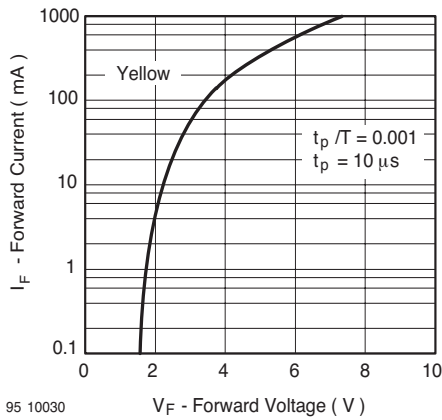


Figure 15. Forward Current vs. Forward Voltage

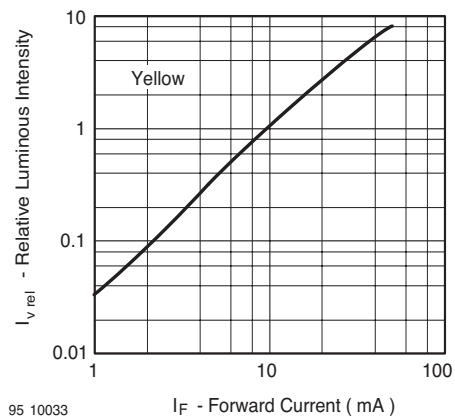


Figure 18. Relative Luminous Intensity vs. Forward Current

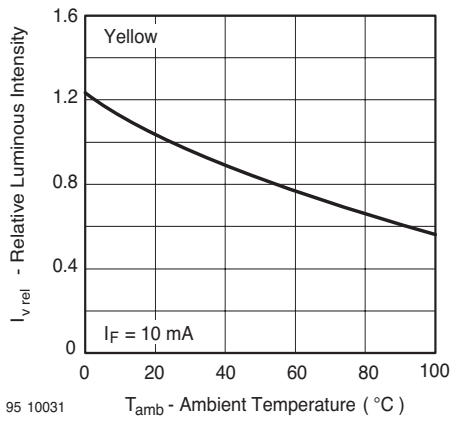


Figure 16. Rel. Luminous Intensity vs. Ambient Temperature

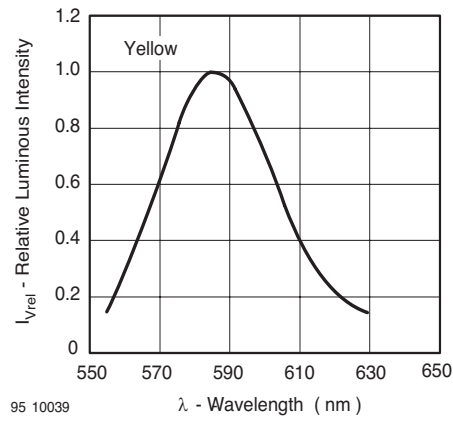


Figure 19. Relative Intensity vs. Wavelength

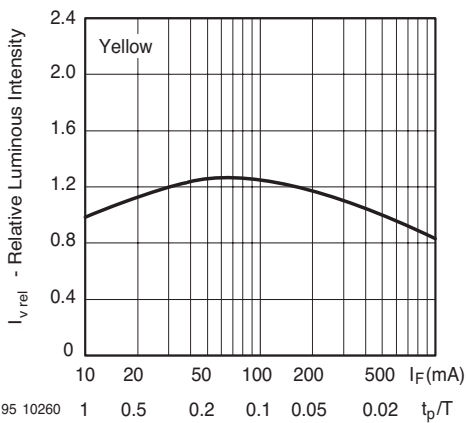


Figure 17. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

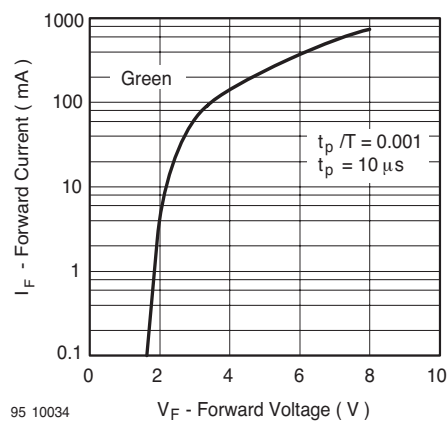


Figure 20. Forward Current vs. Forward Voltage

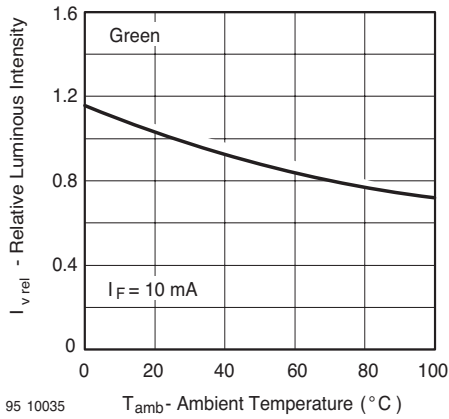


Figure 21. Rel. Luminous Intensity vs. Ambient Temperature

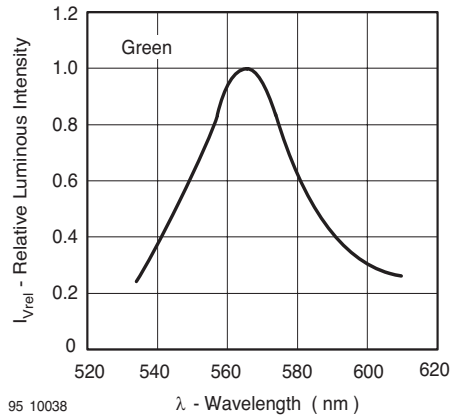


Figure 24. Relative Intensity vs. Wavelength

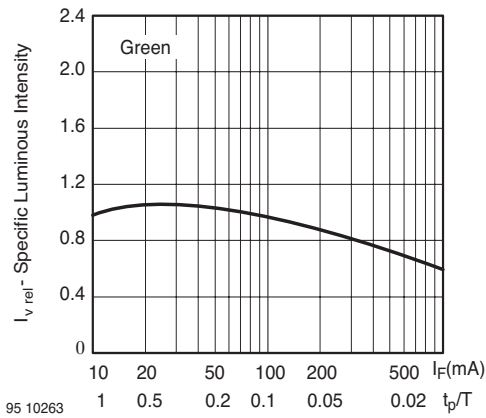


Figure 22. Specific Luminous Intensity vs. Forward Current

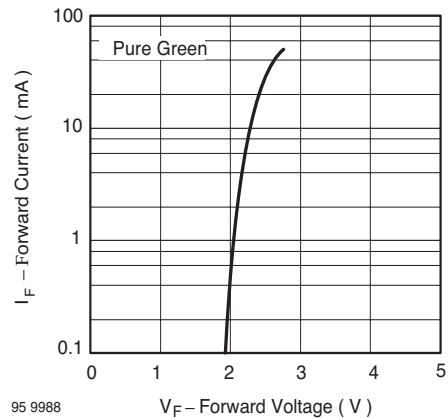


Figure 25. Forward Current vs. Forward Voltage

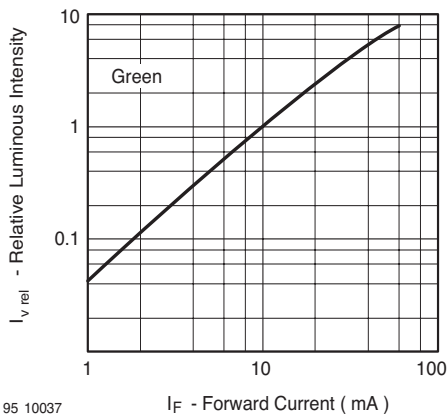


Figure 23. Relative Luminous Intensity vs. Forward Current

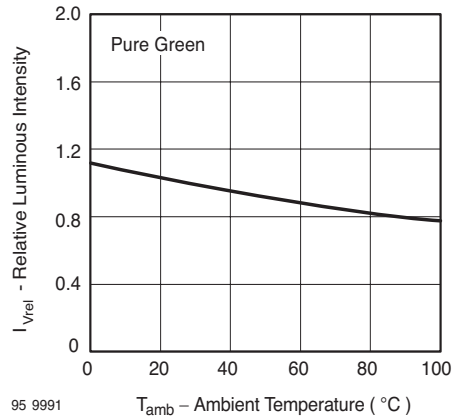


Figure 26. Rel. Luminous Intensity vs. Ambient Temperature

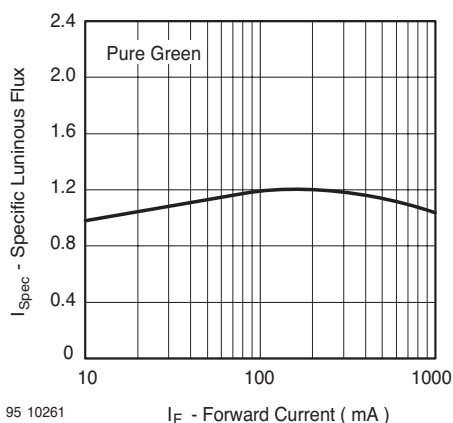


Figure 27. Specific Luminous Intensity vs. Forward Current

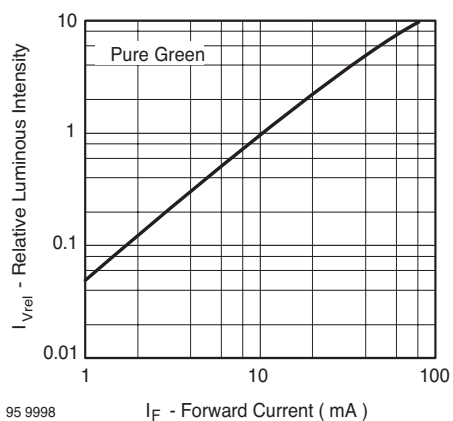


Figure 28. Relative Luminous Intensity vs. Forward Current

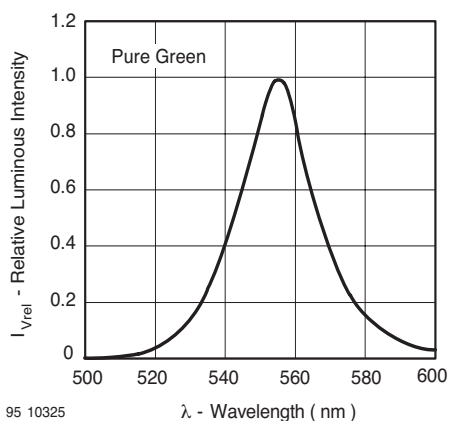
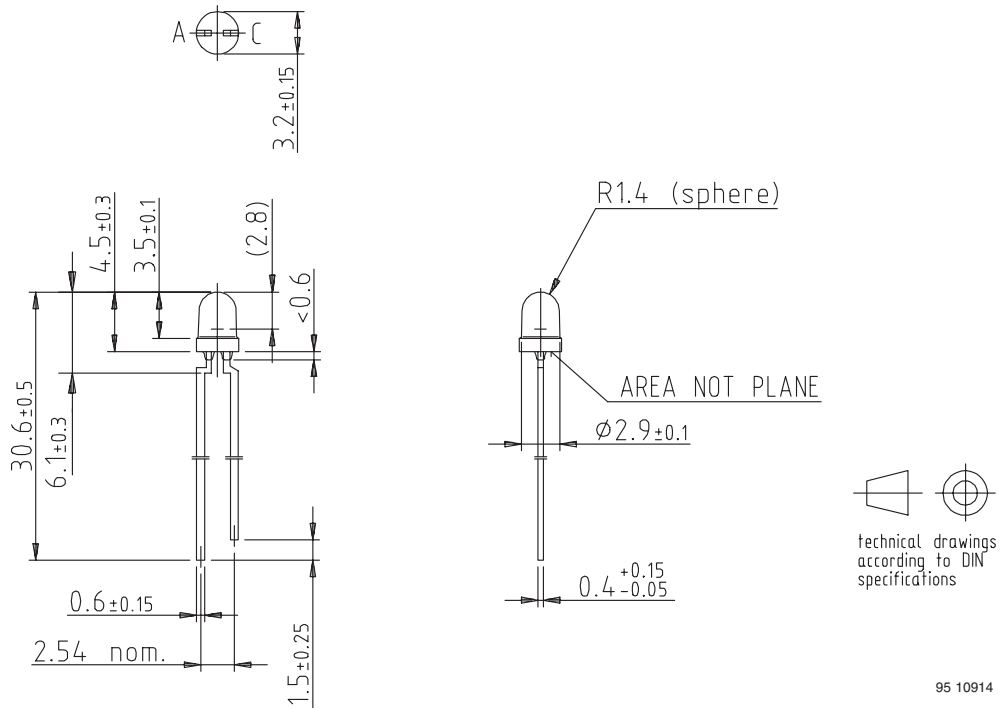


Figure 29. Relative Intensity vs. Wavelength

Package Dimensions in mm



95 10914

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1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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